

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-40 (cancelled).

41. (Previously presented) A method of developing an in-process semiconductor device having a first metal line and a second metal line, comprising:

- placing said device in a deposition and etch surrounding;
- forming a polymer between said first metal line and said second metal line
- providing a layer over said polymer; and
- retaining a state of said polymer.

42. (Previously presented) The method in claim 41, wherein said step of retaining said state of said polymer further comprises having a polymer with a thermal stability sufficient to withstand providing said layer.

43. (Previously presented) The method in claim 42, wherein said step of providing said layer further comprises providing said layer outside of said deposition and etch surrounding.

Claims 44-46 (cancelled).